



IFW

PATENT  
Customer No. 22,852  
Attorney Docket No. 04329.3139

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of: )  
)  
Mitsuaki Izuha et al. ) Group Art Unit: 2811  
)  
Application No.: 10/660,555 ) Examiner: Vu, Quang D.  
)  
Filed: September 12, 2003 )  
) Confirmation No.: 6394  
For: MOSFET FORMED BY USING )  
SALICIDE PROCESS AND )  
METHOD OF MANUFACTURING )  
THE SAME )

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

**INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.97(c)**

Pursuant to 37 C.F.R. §§ 1.56 and 1.97(c), Applicants bring to the attention of the Examiner the documents on the attached listing. To the undersigned's knowledge, this Information Disclosure Statement is being filed after the events recited in Section 1.97(b), but before the mailing date of either a Final action, Quayle action, or a Notice of Allowance. Under the provisions of 37 C.F.R. § 1.97(c), this Information Disclosure Statement includes a certification as specified by Section 1.97(e).

Each document listed in this Information Disclosure Statement was first cited in a communication from the Japanese Patent Office in a counterpart foreign application, and this Information Disclosure Statement is being filed within three months of the mailing date of that communication.

Copies of the listed foreign and non-patent literature documents are attached.

Applicants respectfully request that the Examiner consider the listed documents and indicate that they were considered by making appropriate notations on the attached form.

In lieu of a statement of relevance or translation of the non-English documents, an English language version of the Notification of Reasons for Rejection from the Japanese Patent Office in a corresponding application citing these documents and setting forth the relevance thereof is enclosed.

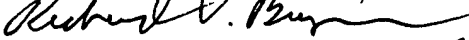
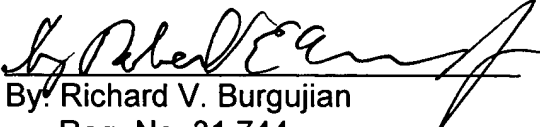
This submission does not represent that a search has been made, or that no better art exists and does not constitute an admission that each or all of the listed documents are material or constitute "prior art." If the Examiner applies any of the documents as prior art against any claims in the application and Applicants determine that the cited documents do not constitute "prior art" under United States law, Applicants reserves the right to present to the office the relevant facts and law regarding the appropriate status of such documents.

Applicants further reserve the right to take appropriate action to establish the patentability of the disclosed invention over the listed documents, should one or more of the documents be applied against the claims of the present application.

If there is any fee due in connection with the filing of this Statement, please charge the fee to our Deposit Account No. 06-0916.

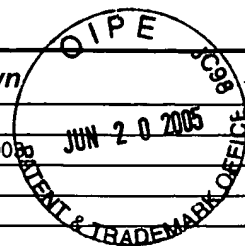
Respectfully submitted,

FINNEGAN, HENDERSON, FARABOW,  
GARRETT & DUNNER, L.L.P.

  
 #27,432  
By: Richard V. Burgujian  
Reg. No. 31,744

Dated: June 20, 2005

IDS Form PTO/SB/08: Substitute for form 1449A/PTO				<b>Complete if Known</b>		
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(Use as many sheets as necessary)</i>				Application Number	10/660,555	
				Filing Date	September 12, 2003	
				First Named Inventor	Mitsuaki Izuha	
				Art Unit	2811	
				Examiner Name	VU, Quang D.	
Attorney Docket Number	4329.3139					
Sheet	1	of	1			



U.S. PATENTS AND PUBLISHED U.S. PATENT APPLICATIONS					
Examiner Initials	Cite No. <sup>1</sup>	Document Number Number-Kind Code <sup>2</sup> (if known)	Issue or Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		US-			
		US-			
		US-			
		US-			
		US-			
		US-			

**Note: Copies of the U.S. Patent Documents are not Required in IDS filed after October 21, 2004**

FOREIGN PATENT DOCUMENTS						
Examiner Initials	Cite No. <sup>1</sup>	Foreign Patent Document Country Code <sup>3</sup> Number <sup>4</sup> Kind Code <sup>5</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	Translation <sup>6</sup>
		JP 2000-150669		Not translated		

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	Translation <sup>6</sup>
		Japanese Patent Office Notification of Reasons for Rejection and English translation thereof. (Appln. #2002-268970)	
		Ja-Hum Ku et al., "High Performance pMOSFETs with Ni(Si <sub>x</sub> Ge <sub>1-x</sub> )/Poly-Si <sub>0.8</sub> Ge <sub>0.2</sub> Gate," 2000 Symposium on VLSI Technology Digest of Technical Papers, 2000, pp. 114 to 115.	
		H. B. Zhao et al., "Interfacial reactions of Ni on Si <sub>1-x</sub> Ge <sub>x</sub> (x=0.2, 0.3) at low temperature by rapid thermal annealing," Journal of Applied Physics, July 1, 2002, Volume 92, Number 1, pp. 214-217.	

Examiner Signature	Date Considered
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.